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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO	
09/891,580	06/26/2001	Toshimitsu Taniguchi	10417-085001	10417-085001 3310	
26211	7590 06/19	003			
FISH & RICHARDSON P.C.			EXAMINER		
45 ROCKEF NEW YORK	CLLER PLAZA, SUITE 2800 NY 10111		ANYA, IGWE U		
			ART UNIT	PAPER NUMBER	
			2825		
			DATE MAILED: 06/19/2003		

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)			
	09/891,580	TANIGUCHI ET AL.			
Office Action Summary	Examiner	Art Unit			
	Igwe U. Anya	2825			
The MAILING DATE of this communication appears on the cover sheet with the correspondence address Period for Reply					
A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely. - If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication. - Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). - Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b). Status					
1) Responsive to communication(s) filed on 10 J	<u>une 2003</u> .				
2a) This action is FINAL. 2b) ☐ This	s action is non-final.				
3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213. Disposition of Claims					
4)⊠ Claim(s) <u>1-12</u> is/are pending in the application	•				
4a) Of the above claim(s) is/are withdrawn from consideration.					
5)⊠ Claim(s) <u>11 and 12</u> is/are allowed.					
6)⊠ Claim(s) <u>1-10</u> is/are rejected.					
7) Claim(s) is/are objected to.					
8) Claim(s) are subject to restriction and/or election requirement.					
Application Papers					
9) The specification is objected to by the Examiner.					
10) ☐ The drawing(s) filed on is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.					
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).					
11) The proposed drawing correction filed on is: a) approved b) disapproved by the Examiner.					
If approved, corrected drawings are required in reply to this Office action.					
12) The oath or declaration is objected to by the Examiner.					
Priority under 35 U.S.C. §§ 119 and 120					
13) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).					
a) All b) Some * c) None of:					
1. Certified copies of the priority documents have been received.					
2. Certified copies of the priority documents have been received in Application No					
 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received. 					
14) Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).					
 a) The translation of the foreign language provisional application has been received. 15) Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121. 					
Attachment(s)					
1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449) Paper No(s)	5) Notice of Informal P	(PTO-413) Paper No(s) latent Application (PTO-152)			
.S. Patent and Trademark Office PTO-326 (Rev. 04-01) Office Ac	tion Summary	Part of Paper No. 11			

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DETAILED ACTION

Claim Rejections - 35 USC § 103

- 1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 2. This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(e), (f) or (g) prior art under 35 U.S.C. 103(a).
- 3. Claims 1 to 10 are rejected under 35 U.S.C. 103(a) as being unpatentable over Lin (US Patent 5502009) in view of Shimizu (US Patent 6380020).
- 4. Lin teaches a substrate having a thin oxide layer (23) and an oxidation resistant film (24), on a first and second device formation regions (21, 22). A photoresist (200) masking the second device formation region is used to remove the oxidation resistant film on the first device formation region, removing the photoresist, removing the oxide layer above the first device formation area using the oxidation resistance film above the second device formation area as a mask (fig 2C), thermally growing a replacement thicker oxide film in the first device region

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using the oxidation resistant film on the second formation region as a mask (fig. 2D), and removing the oxidation resistant mask with any oxide above it on the second formation region by acid etching using phosphoric acid, thereby leaving the thin oxide film in the second device formation area (col. 3 lines 5-60).

- 5. Lin lacks the step of removing the oxide layer on the second device formation region, and forming a new replacement oxide film by thermal oxidation.
- 6. However, Shimizu teaches a step of removing the oxide layer on the second device formation region along with the oxidation resistant film on the second device formation region using a photoresist and replacing with a new oxide layer by thermal oxidation (figs. 2D, 2E, 2F).
- 7. Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to incorporate the teachings of Shimizu in the Lin reference to remove the oxide layer on the second device formation region along with the oxidation resistant film on the second device formation region without a photoresist and form a new oxide layer by thermal oxidation as an art recognized equivalent. Where the general conditions of a claim are disclosed in prior art, provision of adjustability where needed involves only routine skill in the art. In re Stevens, 101USPQ 284 (CCPA 1954).
- 8. Claims 11 and 12 are allowable over the references of record, because none these references teaches or in combination render obvious a method comprising inter alia, implanting a second impurity layer of first conductive type having a low concentration to connect first impurity layer, and implanting a third impurity layer of first conductive type having a high concentration in the first impurity layer.

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Contact Information

9. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Igwe U. Anya whose telephone number is (703) 308-3549. The examiner can normally be reached on M - F 8:30am - 5:00pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Matthew S. Smith can be reached on (703) 308-1323. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 872-9318 for regular communications and (703) 872-9319 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

Igwe U. Anya Examiner Art Unit 2825

IA June 16, 2003

> MATTHEW SMITH SUPERVISORY PATENT EXAMINER TECHNOLOGY CENTER 2800